







THVD1400V SLLSFU3 - OCTOBER 2023

THVD1400V 3-V to 5.5-V RS-485 Transceiver with Flexible I/O Supply, Slew Rate **Control and Integrated IEC ESD Protection**

1 Features

- Meets or exceeds the requirements of the TIA/ EIA-485A standard
- 3-V to 5.5-V RS-485 Supply voltage
- Differential output exceeds 2.1 V for PROFIBUS compatibility with 5-V supply
- 1.65 V to 5.5 V Supply for logic signal interface
- Half-duplex RS-422/RS-485
- Maximum Data rate configurable
 - SLR = High: 500 kbps
 - SLR = Low or floating: 20 Mbps
- Bus I/O protection
 - ±16-kV HBM ESD
 - ±12-kV IEC 61000-4-2 Contact discharge
 - ±12-kV IEC 61000-4-2 Air gap discharge
 - ±4-kV IEC 61000-4-4 Fast transient burst
 - ±16-V bus fault protection (absolute maximum voltage on bus pins)
- Extended industrial temperature range: -40°C to 125°C
- Low power consumption
 - Shutdown supply current < 5 μA
 - Quiescent current during operation < 3 mA
- Glitch-free power-up/power-down for hot plug-in capability
- Open, short, and idle bus failsafe
- 1/8 Unit load (Up to 256 bus nodes)
- Small, space-saving thermally efficient 10-pin VSON package (3 mm x 3 mm)

2 Applications

- Factory automation & control
- **Building automation**
- Motor drives
- Power delivery
- **Industrial transport**
- **HVAC** systems
- **Smart meters**
- Communication Infrastructure

3 Description

The THVD1400V is a half-duplex RS-422/RS-485 transceiver for industrial applications. The device has features such as 3 to 5.5 V bus supply, 1.65 V to 5.5 V low level logic interface support. This device has slew rate select feature that enables it to be used at two maximum speeds based on the SLR pin setting.

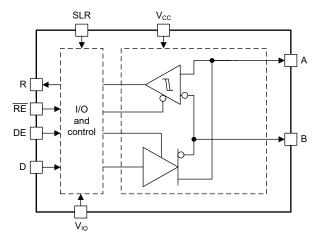
Separate logic supply pin eliminates the need for an additional level shifter when the MCU and RS-485 transceivers are operating with different supplies. The bus pins are immune to high levels of IEC Contact Discharge ESD events eliminating the need for additional system level protection components. The wide common-mode voltage range and low input leakage on bus pins makes the device suitable for multi-point applications over long cable runs.

THVD1400V is available in space-saving thermally efficient 10-VSON package (3 mm x 3 mm). The device is characterized for ambient temperature from -40°C to 125°C.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)
THVD1400V	VSON (10)	3 mm x 3 mm

- For more information, see Section 11.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Simplified Application



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4 Pin Configuration and Functions

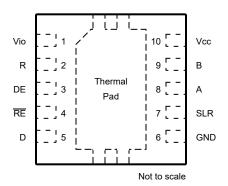


Figure 4-1. VSON (DRC) Package, 10-Pins (Top View)

Table 4-1. Pin Functions

PIN		TVDE	DESCRIPTION
NAME	NO.	TYPE	DESCRIPTION
V _{IO}	1	Logic Supply	Supply for logic I/O signals (R, RE, D, DE, and SLR)
R	2	Digital output	Logic output RS-485 data
DE	3	Digital input	Driver enable/disable. Internal pull-down. Driver disabled by default
RE	4	Digital input	Receiver enable/disable. Internal pull-up. Receiver disabled by default
D	5	Digital input	Logic input RS485 data. Internal pull-up. Drives the bus high by default if driver is enabled
GND	6	GND	Ground
SLR	7	Digital input	Slew rate control. Internal pull-down, default 20 Mbps operation. Logic high SLR enables slow speed (500 kbps)
Α	8	Bus input/output	RS-485 bus pin. This pin is non-inverting driver output or non-inverting receiver input
В	9	Bus input/output	RS-485 bus pin. This pin is inverting driver output or inverting receiver input
V _{CC}	10	Power	3 V to 5.5 V supply
Thermal Pad			Connect to GND for optimal thermal and electrical performance



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1) (2)

		MIN	MAX	UNIT
Logic supply voltage	V _{IO}	-0.5	7	V
Supply voltage	V _{CC}	-0.5	7	V
Bus voltage	Voltage at any bus pin (A or B) with respect to GND	-16	16	V
Differntial bus voltage	Max differential voltage between A and B $V_{DIFF} = (A - B)$	-16	16	V
Input voltage	Range at any logic pin (D, DE, SLR, or $\overline{\text{RE}}$)	-0.3	V _{IO} + 0.2,7	V
Receiver output current	lo	-24	24	mA
Storage temperature	T _{stg}	-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings

				VALUE	UNIT
		Human hady model (HPM) per ANSI/ESDA/	Bus terminals (A, B) and GND	±16,000	V
V _(ESD)	Electrostatic discharge Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾ All pins except bus terminals and GND Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±4,000	V		
		Charged-device model (CDM), per JEDEC specifi	±1,500	V	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings [IEC]

				VALUE	UNIT
V	Electrostatic discharge	Contact discharge, per IEC 61000-4-2	Bus terminals and GND	±12,000	V
V _(ESD)	Liectiostatic discharge	Air-gap discharge, per IEC 61000-4-2	Bus terminals and GND	±12,000	v
$V_{(EFT)}$	Electrical fast transient	Per IEC 61000-4-4	Bus terminals	±4,000	V

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⁽²⁾ All voltage values, except differential I/O bus voltages, are with respect to ground terminal.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		-	MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		3		5.5	V
V _{IO}	I/O supply voltage		1.65		5.5	V
VI	Input voltage at any bus termin	al (separately or common mode) ⁽¹⁾	-7		12	V
V _{IH}	High-level input voltage (D, DE	, RE, SLR inputs)	0.7*V _{IO}		V _{IO}	V
V _{IL}	Low-level input voltage (D, DE	, RE, SLR inputs)	0		0.3*V _{IO}	V
Io	Output current, driver		-60		60	mA
I _{OR}	Output current, receiver	V _{IO} = 1.8 V or 2.5 V	-4		4	mA
I _{OR}	Output current, receiver	V _{IO} = 3.3 V or 5 V	-8		8	mA
R _L	Differential load resistance	·	54	60		Ω
1/4	Cianalina rata	SLR = V _{IO}			500	kbps
R _L	Signaling rate	SLR = GND or floating			20	Mbps
T _A (2)	Operating ambient temperature		-40		125	°C
T _J (2)	Junction temperature		-40		150	°C

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

5.5 Thermal Information

		THVD1400V	
	THERMAL METRIC ⁽¹⁾	DRC (VSON)	UNIT
		10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	53.3	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	60.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	26.6	°C/W
Ψлт	Junction-to-top characterization parameter	2.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	26.5	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	10.4	°C/W

For more information about traditional and new thermalmetrics, see the see the Semiconductor and IC Package Thermal Metrics application report.

5.6 Power Dissipation

	PARAMETER	TEST CONDITION	ONS		Typical	Max	UNIT
В	Driver and receiver enabled,	Unterminated; R_L = 300 Ω , C_L = 50 pF	SLR = H	500 kbps	60	100	mW
PD	V_{CC} = 5.5 V, T_A = 125 °C, D = square wave 50% duty		SLR = L	20Mbps	180	220	mW
	Driver and receiver enabled,	RS-422 load; $R_1 = 100 \Omega$, $C_1 = 50 pF$	SLR = H	500 kbps	100	150	mW
PD	V_{CC} = 5.5 V, T_A = 125 °C, D = square wave 50% duty	, , , , , , , , , , , , , , , , , , , ,	SLR = L	20Mbps	200	250	mW
_	Driver and receiver enabled,	RS-485 load; $R_1 = 54 \Omega$, $C_1 = 50 pF$	SLR = H	500 kbps	175	100 220 150	mW
P _D	V _{CC} = 5.5 V, T _A = 125 °C, D = square wave 50% duty	, , , , , , , , , , , , , , , , , , , ,	SLR = L	20Mbps	250	300	mW

⁽²⁾ Operation is specified for internal (junction) temperatures upto 150°C. Self-heating due to internal power dissipation should be considered for each application. Maximum junction temperature is internally limited by the thermal shut-down (TSD) circuit which disables the driver outputs when the junction temperature reaches typical 170°C.



5.7 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted). All typical values are at 25°C and supply voltage of V_{CC} = 5 V and V_{IO} = 3.3 V, unless otherwise noted.

	PARAMETER	TEST CONDITION	IS	MIN	TYP	MAX	UNIT
Driver							
		$R_L = 60 \Omega$, $-7 V \le V_{test} \le 12 V$ (See Figure 6-1)	1.5	3.3		V
		$R_L = 60 \Omega, -7 V \le V_{test} \le 12 V, 4.5 V \le V_{CC} \le 5.$		2.1	3.3		V
V _{OD}	Driver differential output	$R_L = 100 \Omega$ (See Figure 6-2)		2	4		V
· ODI	voltage magnitude	$R_L = 54 \Omega$, $4.5 V \le V_{CC} \le 5.5 V$ (See Figure 6-2	2.1	3.3		V	
		$R_L = 54 \Omega$ (See Figure 6-2)	• /	1.5	3.3		
	Change in magnitude of	11(- 34 12 (See Figure 0-2)		1.5	J.J		v
Δ V _{OD}	Change in magnitude of differential output voltage	R_L = 54 Ω or 100 Ω (See Figure 6-2)		-50		50	mV
V _{OC}	Common-mode output voltage	R_L = 54 Ω or 100 Ω (See Figure 6-2)	54 Ω or 100 Ω (See Figure 6-2)		V _{CC} /2	3	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage	R_L = 54 Ω or 100 Ω (See Figure 6-2)		-50		50	mV
V _{OC(PP)}	Peak-to-peak common- mode output voltage	R_L = 54 Ω , V_{CC} = 3.3 V, DE = H, D = 20 Mbps 6-2)	square wave (See Figure		375		mV
los	Short-circuit output current	DE = V_{IO} , -7 V \leq (V_A or V_B) \leq 12 V, or A shorted	d to B	-250		250	mA
Receiver	1	1					
			V _I = 12 V		85	100	μA
l _l	Bus input current	DE = 0 V, V_{CC} and V_{IO} = 0 V or 5.5 V	V ₁ = -7 V	-100	-70		μA
V _{TH+}	Positive-going input threshold voltage ⁽¹⁾			100	- 85	- 45	mV
V _{TH-}	Negative-going input threshold voltage ⁽¹⁾	Over common-mode range of - 7 V to 12 V		-200	-150		mV
	-			0.5			\
V _{HYS}	Input hysteresis			25	50		mV
C _{A,B}	Input differential capacitance	Measured between A and B, f = 1 MHz			20		pF
V _{OH}	Output high voltage	$I_{OH} = -8 \text{ mA}, V_{IO} = 3 \text{ to } 3.6 \text{ V or } 4.5 \text{ V to } 5.5 \text{ V}$		V _{IO} – 0.4	V _{IO} – 0.2		V
V _{OL}	Output low voltage	I_{OL} = 8 mA, V_{IO} = 3 to 3.6 V or 4.5 V to 5.5 V			0.2	0.4	V
V _{OH}	Output high voltage	$I_{OH} = -4$ mA, $V_{IO} = 1.65$ to 1.95 V or 2.25 V to 2	2.75 V	V _{IO} - 0.4	V _{IO} – 0.2		V
V _{OL}	Output low voltage	I _{OL} = 4 mA, V _{IO} = 1.65 to 1.95 V or 2.25 V to 2.	75 V		0.2	0.4	V
loz	Output high-impedance current, R pin	$V_O = 0 \text{ V or } V_{IO}, \overline{RE} = V_{IO}$		-2		2	μA
Logic							
l _{IN}	Input current (D, RE, DE , SLR)	$3 \text{ V} \le \text{V}_{1O} \le 5.5 \text{ V}, 0 \text{ V} \le \text{V}_{1N} \le \text{V}_{1O}$		-5		5	μA
Thormal I	Protection						
						1	
T _{SHDN}	Thermal shutdown threshold	Temperature rising		150	170		°C
T _{HYS}	Thermal shutdown hysteresis				15		°C
Supply							
UV _{VCC}	Rising under-voltage threshold on V _{CC}				2.5	2.7	V
JV _{VCC}	Falling under-voltage threshold on V _{CC}			2	2.1		V
UV _{VCC(hys}	11				400		mV
UV _{VIO}	Rising under-voltage threshold on V _{IO}				1.4	1.6	V
JV _{VIO}	Falling under-voltage threshold on V _{IO}			1.2	1.3		V
JV _{VIO(hys)}	Liveteresia en under veltere			-	100		mV



5.7 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted). All typical values are at 25°C and supply voltage of V_{CC} = 5 V and V_{IO} = 3.3 V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
		Driver and receiver enabled	RE = 0 V, DE = V _{IO} , No load		1.5	3	mA
	Supply current (quiescent),	Driver enabled, receiver disabled	RE = V _{IO} , DE = V _{IO} , No load		1.4	2.5	mA
Icc	V _{CC} = 4.5 V to 5.5 V	Driver disabled, receiver enabled	RE = 0 V, DE = 0 V, No load		0.8	1.25	mA
		Driver and receiver disabled	RE = V _{IO} , DE = 0 V, D = open, No load		0.2	4	μΑ
		Driver and receiver enabled	RE = 0 V, DE = V _{IO} , No load		1.4	2.1	mA
	Supply current (quiescent),	Driver enabled, receiver disabled	RE = V _{IO} , DE = V _{IO} , No load		1	1.6	mA
Icc	V _{CC} = 3 V to 3.6 V	Driver disabled, receiver enabled	RE = 0 V, DE = 0 V, No load		0.7	1.1	mA
		Driver and receiver disabled	RE = V _{IO} , DE = 0 V, D = open, No load		0.2	4	μΑ
		Driver disabled, Receiver enabled, SLR = GND	DE = 0 V, RE = 0 V, No load		10	18	μΑ
	Logic supply current (quiescent), V _{IO} = 3 V to 3.6	Driver disabled, Receiver enabled, SLR = V _{IO}	DE = 0 V, RE = 0 V, No load		13	22	μΑ
I _{IO}	V	Driver disabled, Receiver disabled, SLR = GND	DE = 0 V, RE = V _{IO} , No load		2	3	μA
		Driver disabled, Receiver disabled, SLR = V _{IO}	DE = 0 V, RE = V _{IO} , No load		5	7	μΑ

⁽¹⁾ V_{TH+} is specified to be at least V_{HYS} higher than V_{TH-} .



5.8 Switching Characteristics_500 kbps

500-kbps (with SLR = V_{IO}) over recommended operating conditions. All typical values are at 25°C and supply voltage of V_{CC} = 5 V and V_{IO} = 3.3 V, unless otherwise noted.

	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT	
Driver			1					
	Differential output rise/fall time		V _{CC} = 3 to 3.6 V, Typical at 3.3V	200	250	600	ns	
t _r , t _f	Differential output rise/fall time		V _{CC} = 4.5 to 5.5 V, Typical at 5 V	200	270	600	ns	
t _{PHL} , t _{PLH}	Propagation delay	$R_L = 54 \Omega, C_L = 50 pF$	V _{CC} = 3 to 3.6 V, Typical at 3.3V		200	500	ns	
PHL, PLH	Propagation delay	See Figure 6-3	V _{CC} = 4.5 to 5.5 V, Typical at 5 V		180	450	ns	
	Pulse skew, t _{PHL} - t _{PLH}		V _{CC} = 3 to 3.6 V, Typical at 3.3V		2	15	ns	
t _{SK(P)}			V _{CC} = 4.5 to 5.5 V, Typical at 5 V		2	15	ns	
t _{PHZ} , t _{PLZ}	Disable time	RE = X			80	200	ns	
t _{PHZ} , t _{PLZ}		E 11 c	RE = 0 V	See Figure 6-4 and Figure 6-5		200	650	ns
TPZH, TPZL	Enable time	RE = V _{IO}	and rigure 0-0		6	13	μs	
Receiver								
t _r , t _f	Output rise/fall time				5	20	ns	
t _{PHL} , t _{PLH}	Propagation delay	C _L = 15 pF	See Figure 6-6		30	90	ns	
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}				4	6	ns	
t _{PHZ} , t _{PLZ}	Disable time	DE = X, V _{IO} < 3 V			20	65	ns	
t _{PHZ} , t _{PLZ}	Disable time	DE = X, V _{IO} ≥ 3 V				50	ns	
t _{PZH(1)} , t _{PZL(}	Enable time	DE = V _{IO} , V _{IO} < 3 V	See Figure 6-7		80	170	ns	
t _{PZH(1),} t _{PZL(}	Enable time	DE = V _{IO} , V _{IO} ≥ 3 V			80	155	ns	
$t_{PZH(2)}$, $t_{PZL(2)}$	Enable time	DE = 0 V	See Figure 6-8		7	14	μs	



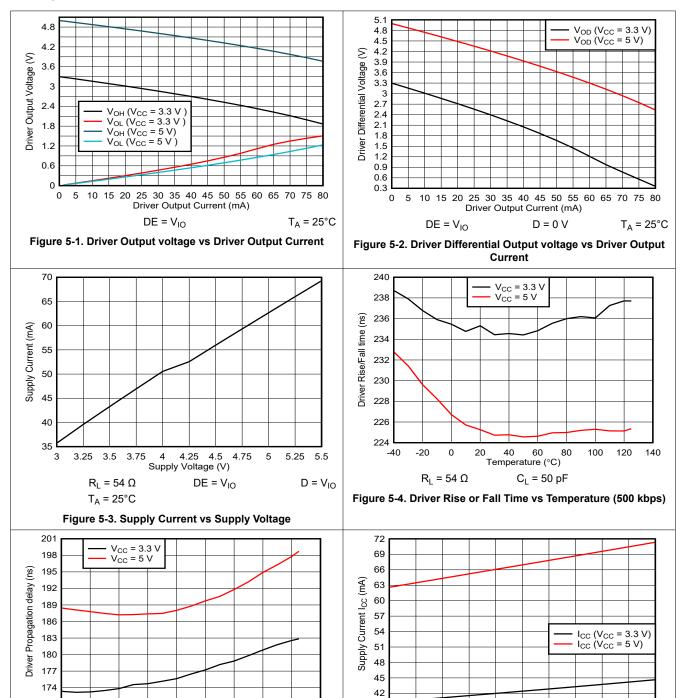
5.9 Switching Characteristics_20 Mbps

20-Mbps (SLR = GND) over recommended operating conditions. All typical values are at 25° C and supply voltage of $V_{CC} = 5$

PARAMETER		TEST COND	TIONS	MIN TYP	MAX	UNIT
Driver						
t _r , t _f	Differential output rise/fall time		V _{CC} = 3 to 3.6 V, Typical at 3.3 V	6	5 15	ns
प, प 	Differential output rise/fall time		V _{CC} = 4.5 to 5.5 V, Typical at 5 V	6	5 15	ns
.	Propagation dolay	$R_L = 54 \Omega, C_L = 50 pF$	V _{CC} = 3 to 3.6 V, Typical at 3.3 V	25	5 50	ns
$t_{\text{PHL}},t_{\text{PLH}}$ Propagation delay $t_{\text{SK(P)}}$ Pulse skew, $ t_{\text{PHL}} - t_{\text{PLH}} $	See Figure 6-3	V _{CC} = 4.5 to 5.5 V, Typical at 5 V	20) 40	ns	
		V _{CC} = 3 to 3.6 V, Typical at 3.3 V	,	1 6	ns	
^L SK(P)	r uise skew, [tpHL — tpLH]		V _{CC} = 4.5 to 5.5 V, Typical at 5 V		1 6	ns
t _{PHZ} , t _{PLZ}	Disable time	RE = X		25	5 50	ns
t _{PZH} , t _{PZL} E	Enable time	RE = 0 V	See Figure 6-4	30	70	ns
		$\overline{RE} = V_{IO}$, $V_{IO} = 1.65$ V to 2.75 V	and Figure 6-5	(3 13	μs
		$\overline{RE} = V_{IO}$, $V_{IO} = 3 \text{ V to } 5.5 \text{ V}$	(3 13	μs	
Receiver						
t _r , t _f	Output rise/fall time	C _L = 15 pF		5	5 10	ns
t _{PHL} , t _{PLH}	Propagation delay	C _L = 15 pF	0 Figure 0.0	30	90	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}	C _L = 15 pF, V _{IO} < 2.25 V	See Figure 6-6		6	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}	C _L = 15 pF, V _{IO} ≥ 2.25 V			8	ns
t _{PHZ} , t _{PLZ}	Disable time	DE = X, V _{IO} < 3 V		20) 65	ns
t _{PHZ} , t _{PLZ}	Disable time	DE = X, V _{IO} ≥ 3 V			50	ns
t _{PZH(1)} , t _{PZL(}	Enable time	$\overline{RE} = V_{IO}, V_{IO} = 3 \text{ V to } 5.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 15 \text{ pF}, V_{IO} < 2.25 \text{ V}$ $C_L = 15 \text{ pF}, V_{IO} \ge 2.25 \text{ V}$ $DE = X, V_{IO} \le 3 \text{ V}$ $DE = X, V_{IO} \ge 3 \text{ V}$ $DE = V_{IO}, V_{IO} \le 3 \text{ V}$ $DE = V_{IO}, V_{IO} \le 3 \text{ V}$	See Figure 6-7	80) 170	ns
t _{PZH(1),} t _{PZL(}	Enable time	DE = V _{IO,} V _{IO} ≥ 3 V		80) 155	ns
$\begin{array}{l}t_{PZH(2)},\\t_{PZL(2)}\end{array}$	Enable time	DE = 0 V	See Figure 6-8	(5 14	μs



5.10 Typical Characteristics



 $R_L = 54 \Omega$

20 40 60 Temperature (°C)

Figure 5-5. Driver Propagation Delay vs Temperature (500 kbps)

 $C_L = 50 pF$

100

120

Data Frequency (Mhz)

Figure 5-6. Supply Current vs Signal Rate (500 kbps)

T_A = 25 °C

171

-40

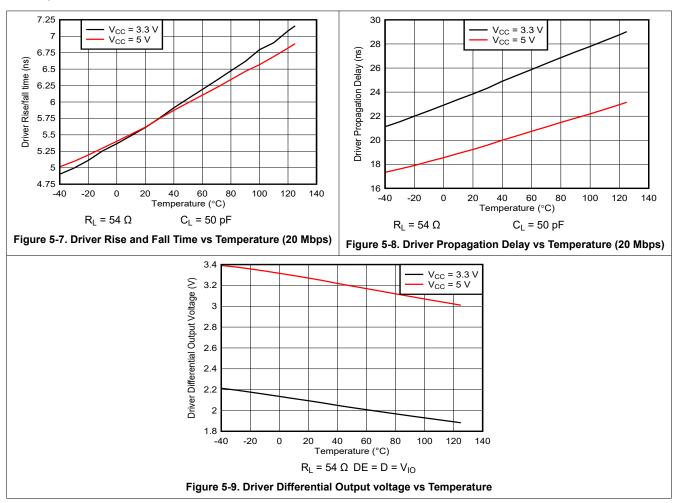
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0

 $R_1 = 54 \Omega$



5.10 Typical Characteristics (continued)





6 Parameter Measurement Information

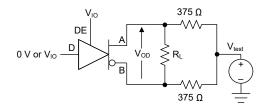


Figure 6-1. Measurement of Driver Differential Output Voltage With Common-Mode Load

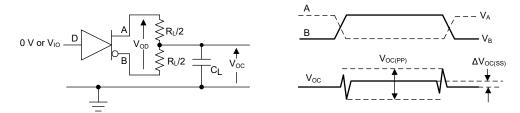


Figure 6-2. Measurement of Driver Differential and Common-Mode Output With RS-485 Load

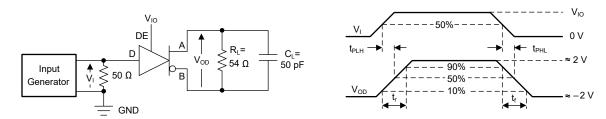


Figure 6-3. Measurement of Driver Differential Output Rise and Fall Times and Propagation Delays

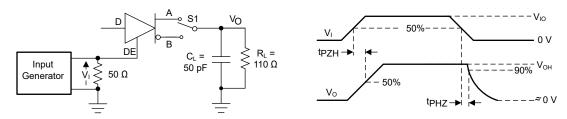


Figure 6-4. Measurement of Driver Enable and Disable Times With Active High Output and Pull-Down Load

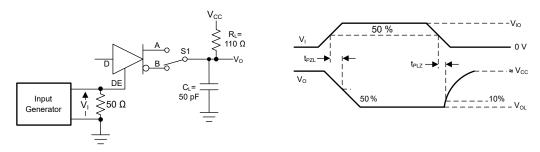


Figure 6-5. Measurement of Driver Enable and Disable Times With Active Low Output and Pull-up Load

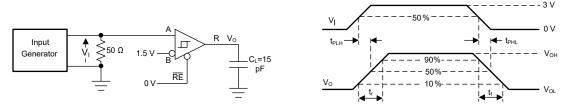


Figure 6-6. Measurement of Receiver Output Rise and Fall Times and Propagation Delays

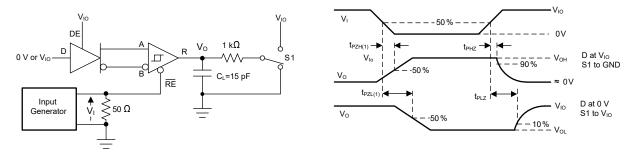


Figure 6-7. Measurement of Receiver Enable/Disable Times With Driver Enabled

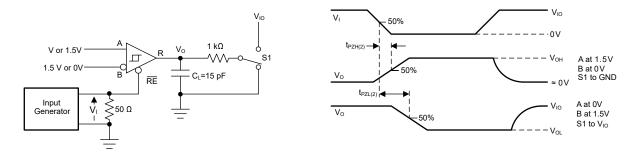


Figure 6-8. Measurement of Receiver Enable Times With Driver Disabled

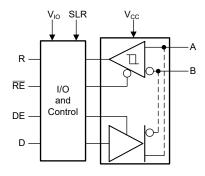


7 Detailed Description

7.1 Overview

The THVD1400V is a half duplex RS-485 transceiver. The device has slew rate control pin SLR which can be used to set the device in maximum 20 Mbps mode or slew rate limited 500 kbps mode. THVD1400V also has low level logic interface V_{IO} pin to run RS-485 bus at 3 to 5.5 V supply, while the microcontroller can be at any voltage between 1.65 V to 5.5 V. This feature eliminates any level shifter that may be otherwise needed between the microcontroller and the RS-485 transceiver.

7.2 Functional Block Diagrams



7.3 Feature Description

The THVD1400V operates from 3 V to 5.5 V bus supply and 1.65 to 5.5 V logic supply. For applications wanting to keep same bus supply and logic supply, V_{CC} and V_{IO} can be shorted on PCB. Internal ESD protection circuits on bus pins protect the transceiver against Electrostatic Discharges (ESD) according to IEC 61000-4-2 of up to ± 12 kV (Contact Discharge), ± 12 kV (Air Gap Discharge) and against electrical fast transients (EFT) according to IEC 61000-4-4 of up to ± 4 kV.

7.4 Device Functional Modes

When the driver enable pin, DE, is logic high, the differential outputs A and B follow the logic states at data input D. A logic high at D causes A to turn high and B to turn low. In this condition, the differential output voltage defined as $V_{OD} = V_A - V_B$ is positive. When D is low, the output states reverse, B turns high, A becomes low, and V_{OD} is negative.

When DE is low, both outputs turn high-impedance. In this condition, the logic state at D is irrelevant. The DE pin has an internal pull-down resistor to ground; thus, when left open, the driver is disabled (high-impedance) by default. The D pin has an internal pull-up resistor to V_{IO} , thus, when left open while the driver is enabled, output A turns high and B turns low.

INPUT OUTPUTS ENABLE FUNCTION D DE Α В Н L Н Н Actively drive bus high L Н L Н Actively drive bus low Ζ Ζ Driver disabled Χ Z Χ OPEN Ζ Driver disabled by default **OPEN** Н Н L Actively drive bus high by default

Table 7-1. Driver Function Table

When the receiver enable pin, \overline{RE} , is logic low, the receiver is enabled. When the differential input voltage defined as $V_{ID} = V_A - V_B$ is positive and higher than the positive input threshold, V_{TH+} , the receiver output, R, turns high. When V_{ID} is negative and lower than the negative input threshold, V_{TH-} , the receiver output, R, turns low. If V_{ID} is between V_{TH+} and V_{TH-} the output is indeterminate.

When \overline{RE} is logic high or left open, the receiver output is high-impedance and the magnitude and polarity of V_{ID} are irrelevant. Internal biasing of the receiver inputs causes the output to go fail safe-high when the transceiver is disconnected from the bus (open-circuit), the bus lines are shorted (short-circuit), or the bus is not actively driven (idle bus).

OUTPUT **DIFFERENTIAL INPUT ENABLE FUNCTION** RE $V_{ID} = V_A - V_B$ R $V_{TH+} < V_{ID}$ L Н Receive valid bus high ? $V_{TH-} < V_{ID} < V_{TH+}$ L Indeterminate bus state $V_{ID} < V_{TH-}$ L L Receive valid bus low Χ Н Ζ Receiver disabled Х **OPEN** Z Receiver disabled by default

Н

Н

Н

Fail-safe high output

Fail-safe high output

Fail-safe high output

L

L

L

Table 7-2. Receiver Function Table

7.4.1 Operational Data rate

Open-circuit bus

Short-circuit bus

Idle (terminated) bus

THVD1400V can be used in slow speed or fast speed RS-485 networks by configuring Slew rate control (SLR) pin. Table 7-3 describes slew rate control function.

	Table 7-3. Siew rate control function table									
Signal state	Driver	Receiver	Comment							
SLR = V _{IO}	Maximum speed of operation = 500kbps	Maximum speed of operation = 500kbps	Active high slew rate limiting applied on driver output and glitch filter in receiver path enabled							
SLR = GND or floating	Maximum speed of operation = 20Mbps	Maximum speed of operation = 20Mbps	Slew rate limiting on driver output disabled and glitch filter in receiver path disabled							

Table 7-3. Slew rate control function table

7.4.2 Protection Features

THVD1400V has in-built protection features such as supply undervoltage, bus short circuit and thermal shutdown.

Supply undervoltage protection is present on both V_{CC} and V_{IO} supply. This maintains the bus output and receiver logic output in known driven state when the supply is above the rising undervoltage threshold. Table 7-4 describes the device behavior in various scenarios of supply levels.

Table 7-4. Supply Function Table

V _{CC}	V _{IO}	Driver Output	Receiver Output		
> UV _{VCC(rising)}	> UV _{VIO(rising)}	Determined by DE and D inputs	Determined by RE and A-B		
< UV _{VCC(falling)}	> UV _{VIO(rising)}	High impedance	Undetermined		
> UV _{VCC(rising)}	< UV _{VIO(falling)}	High impedance	High impedance		
< UV _{VCC(falling)}	< UV _{VIO(falling)}	High impedance	High impedance		

Bus terminals are protected against high voltage short circuit events up to \pm 16 V. Additionally, bus short circuit current is limited to 250 mA. In events like bus contention when multiple drivers are driving the bus simultaneously, the current through the bus terminals is internally limited. If the power dissipation makes the junction temperature cross 150°C, thermal shutdown is activated which disables the driver and receiver and reduces the on-chip power dissipation. The device is enabled once the junction temperature falls by the thermal shutdown hysteresis as specified in electrical parameter section of the data sheet.



8 Application Information Disclaimer

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The THVD1400V is a half duplex RS-485 transceiver used for asynchronous data transmissions. The driver and receiver enable pins, slew rate control pins allow the device to be applicable for various point-to-point, multipoint or multidrop network configurations.

8.2 Typical Application

An RS-485 bus consists of multiple transceivers connecting in parallel to a bus cable. To eliminate line reflections, each cable end is terminated with a termination resistor, R_T , whose value matches the characteristic impedance, Z_0 , of the cable. This method, known as parallel termination, allows for higher data rates over longer cable length. Figure 8-1 shows the two end nodes terminated, while remaining nodes are unterminated.

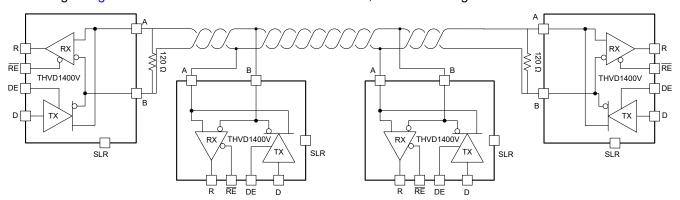


Figure 8-1. Typical Half Duplex RS-485 Network With all Nodes Using THVD1400V

8.2.1 Design Requirements

RS-485 is a robust electrical standard suitable for long-distance networking that may be used in a wide range of applications with varying requirements, such as distance, data rate, and number of nodes.

8.2.1.1 Data Rate and Bus Length

There is an inverse relationship between data rate and cable length, which means the higher the data rate, the shorter the cable length; and conversely, the lower the data rate, the longer the cable length. While most RS-485 systems use data rates between 10 kbps and 100 kbps, some applications require data rates up to 300 kbps at distances of 4000 feet and longer. Longer distances are possible by allowing for small signal jitter of up to 5% or 10%.

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8.2.1.2 Stub Length

When connecting a node to the bus, the distance between the transceiver inputs and the cable trunk, known as the stub, should be as short as possible. Stubs present a non-terminated piece of bus line which can introduce reflections as the length of the stub increases. As a general guideline, the electrical length, or round-trip delay, of a stub should be less than one-tenth of the rise time of the driver, thus giving a maximum physical stub length as shown in Equation 1.

$$L_{(STUB)} \le 0.1 \times t_r \times v \times c \tag{1}$$

where:

- t_r is the 10/90 rise time of the driver
- c is the speed of light $(3 \times 10^8 \text{ m/s})$
- *v* is the signal velocity of the cable or trace as a factor of *c*

THVD1400V can be used in both slow speed and high speed networks with SLR pin configurability. Slew rate limiting makes the driver output rise or fall time slower so that stub lengths can be increased.

8.2.1.3 Bus Loading

The RS-485 standard specifies that a compliant driver must be able to driver 32 unit loads (UL), where 1 unit load represents a load impedance of approximately 12 k Ω . Because the THVD1400V consists of 1/8 UL transceivers, connecting up to 256 transceivers to the bus is possible.

8.2.1.4 Receiver Failsafe

The differential receiver of the THVD1400V is failsafe to invalid bus states caused by the following:

- · Open bus conditions, such as a disconnected connector
- · Shorted bus conditions, such as cable damage shorting the twisted-pair together
- Idle bus conditions that occur when no driver on the bus is actively driving

In any of these cases, the differential receiver outputs a failsafe logic high state so that the output of the receiver is not indeterminate.

Receiver failsafe is accomplished by offsetting the receiver thresholds such that the *input indeterminate* range does not include zero volts differential. To comply with the RS-422 and RS-485 standards, the receiver output must output a high when the differential input V_{ID} is more positive than 200 mV, and must output a low when V_{ID} is more negative than -200 mV. The receiver parameters which determine the failsafe performance are V_{TH+} , V_{TH-} , and V_{HYS} (the separation between V_{TH+} and V_{TH-}). As shown in the Table 7-2, differential signals more negative than -200 mV always causes a low receiver output, and differential signals more positive than 200 mV always causes a high receiver output.

When the differential input signal is close to zero, it is still above the V_{TH+} threshold, and the receiver output is high. Only when the differential input is more than V_{HYS} below V_{TH+} does the receiver output transition to a low state. Therefore, the noise immunity of the receiver inputs during a bus fault conditions includes the receiver hysteresis value, V_{HYS} , as well as the value of V_{TH+} .



8.2.1.5 Transient Protection

The bus pins of the THVD1400V transceiver family include on-chip ESD protection against ± 16 -kV HBM and ± 12 -kV IEC 61000-4-2 contact discharge. The International Electrotechnical Commission (IEC) ESD test is far more severe than the HBM ESD test. The 50% higher charge capacitance, $C_{(S)}$, and 78% lower discharge resistance, $R_{(D)}$, of the IEC model produce significantly higher discharge currents than the HBM model.

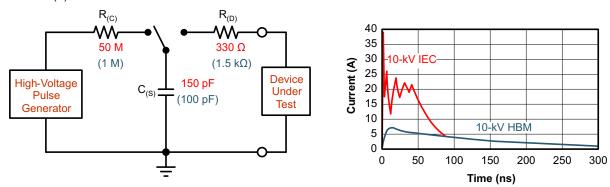


Figure 8-2. HBM and IEC ESD Models and Currents in Comparison (HBM Values in Parenthesis)

The on-chip implementation of IEC ESD protection significantly increases the robustness of equipment. Common discharge events occur because of human contact with connectors and cables. Designers may choose to implement protection against longer duration transients, typically referred to as surge transients.

EFTs are generally caused by relay-contact bounce or the interruption of inductive loads. Surge transients often result from lightning strikes (direct strike or an indirect strike which induce voltages and currents), or the switching of power systems, including load changes and short circuit switching. These transients are often encountered in industrial environments, such as factory automation and power-grid systems.

Figure 8-3 compares the pulse-power of the EFT and surge transients with the power caused by an IEC ESD transient. The left side of the diagram shows the relative pulse-power for a 0.5-kV surge transient and 4-kV EFT transient, both of which exceed the 10-kV ESD transient visible in the lower-left corner. 500-V surge transients are representative of events that may occur in factory environments in industrial and process automation.

The right side of the diagram shows the pulse-power of a 6-kV surge transient, relative to the same 0.5-kV surge transient. 6-kV surge transients may occur in power generation and power-grid systems.

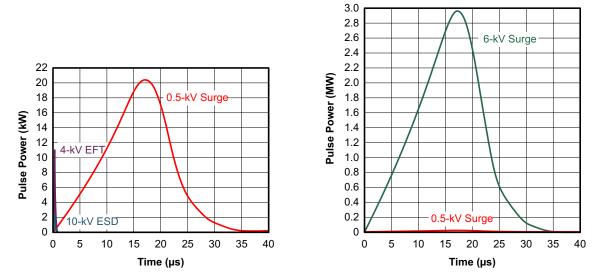


Figure 8-3. Power Comparison of ESD, EFT, and Surge Transients

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For surge transients, high-energy content is characterized by long pulse duration and slow decaying pulse power. The electrical energy of a transient that is dumped into the internal protection cells of a transceiver is converted into thermal energy, which heats and destroys the protection cells, thus destroying the transceiver. Figure 8-4 shows the large differences in transient energies for single ESD, EFT, surge transients, and an EFT pulse train that is commonly applied during compliance testing.

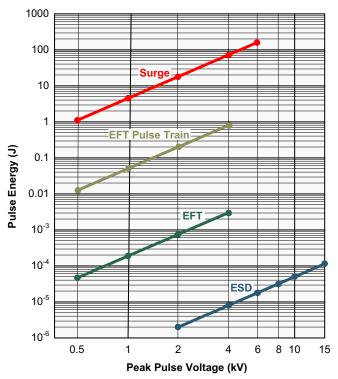


Figure 8-4. Comparison of Transient Energies



8.2.2 Detailed Design Procedure

To protect bus nodes against high-energy surge transients, the implementation of external transient protection devices is necessary. Figure 8-5 suggests a protection circuit against 1 kV surge (IEC 61000-4-5) transients. Table 8-1 shows the associated bill of materials.

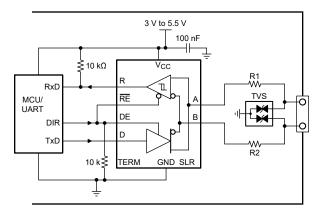


Figure 8-5. Transient Protection Against Surge Transients for THVD1400V

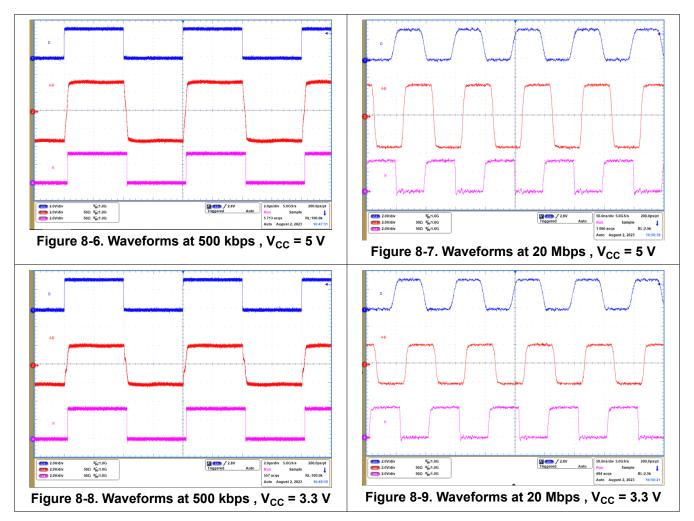
Table 8-1. Bill of Materials

DEVICE	FUNCTION	ORDER NUMBER	MANUFACTURER ⁽¹⁾		
XCVR	RS-485 transceiver	THVD1400V	TI		
R1	10.0 pulse proof thick film register	CRCW0603010RJNEAHP	Vichov		
R2	-10-Ω, pulse-proof thick-film resistor	CKCW00030 TOKJINEARP	Vishay		
TVS	Bidirectional 400-W transient suppressor	CDSOT23-SM712	Bourns		

(1) See the Third Part Disclaimer.



8.2.3 Application Curves



8.3 Power Supply Recommendations

For reliable operation at all data rates and supply voltages, each supply should be decoupled with a 100 nF ceramic capacitor located as close to the supply pin as possible. This helps to reduce supply voltage ripple present on the outputs of switched-mode power supplies and also helps to compensate for the resistance and inductance of the PCB power planes.

8.4 Layout

8.4.1 Layout Guidelines

Robust and reliable bus node design often requires the use of external transient protection devices in order to protect against surge transients that may occur in industrial environments. Since these transients have a wide frequency bandwidth (from approximately 3 MHz to 300 MHz), high-frequency layout techniques should be applied during PCB design.

- 1. Place the protection circuitry close to the bus connector to prevent noise transients from propagating across the board.
- 2. Use V_{CC} and ground planes to provide low inductance. Note that high-frequency currents tend to follow the path of least impedance and not the path of least resistance.
- 3. Design the protection components into the direction of the signal path. Do not force the transient currents to divert from the signal path to reach the protection device.
- 4. Apply atleast 100 nF decoupling capacitors as close as possible to the V_{CC} and V_{IO} pin of the transceiver, UART and/or controller ICs on the board.
- 5. Use at least two vias for V_{CC} and ground connections of decoupling capacitors and protection devices to minimize effective via inductance.
- 6. Use $1-k\Omega$ to $10-k\Omega$ pull-up and pull-down resistors for logic lines to limit noise currents in these lines during transient events.
- 7. Insert pulse-proof resistors into the A and B bus lines if the TVS clamping voltage is higher than the specified maximum voltage of the transceiver bus pins. These resistors limit the residual clamping current into the transceiver and prevent it from latching up.
- 8. While pure TVS protection is sufficient for surge transients up to 1 kV, higher transients require metal-oxide varistors (MOVs) which reduce the transients to a few hundred volts of clamping voltage, and transient blocking units (TBUs) that limit transient current to less than 1 mA.

8.4.2 Layout Example

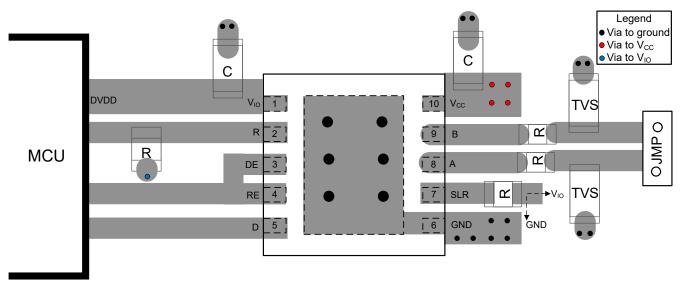


Figure 8-10. Layout Example for THVD1400V in VSON-10 Package

9 Device and Documentation Support

9.1 Device Support

9.1.1 Third-Party Products Disclaimer

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES				
October 2023	*	Initial Release				

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
THVD1400VDRCR	ACTIVE	VSON	DRC	10	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1400V	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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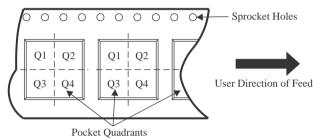
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THVD1400VDRCR	VSON	DRC	10	5000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
١	THVD1400VDRCR	VSON	DRC	10	5000	367.0	367.0	35.0	

3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



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NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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